

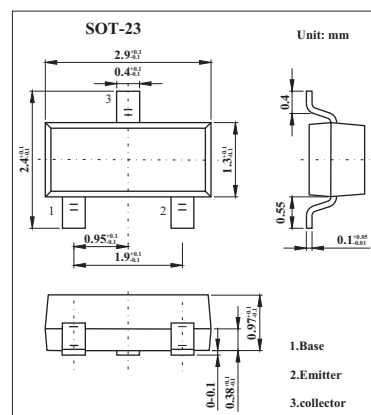
PNP Silicon Transistor

2SA733

Features

Collector Power dissipation: $P_C=200\text{mW}$

Collector Current : $I_C=-150\text{mA}$



Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	-60	V
Collector to emitter voltage	V_{CEO}	-50	V
Emitter to base voltage	V_{EBO}	-5.0	V
Collector Current (DC)	I_C	-150	mA
Power dissipation	P_C	200	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test conditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	$I_C = -5\mu\text{A}, I_E = 0$	-60			V
Collector-emitter breakdown voltage	V_{CEO}	$I_C = -1\text{mA}, I_B = 0$	-50			V
Emitter-base breakdown voltage	V_{EBO}	$I_E = -50\mu\text{A}, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -60\text{V}, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -6\text{V}, I_C = -1\text{mA}$	120		475	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100\text{mA}, I_B = -10\text{mA}$		-0.18	-0.3	V
Base-emitter voltage	$V_{BE(on)}$	$V_{CE} = -6\text{V}, I_C = -1.0\text{mA}$	-0.58	-0.62	-0.68	V
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$		4.5	7	pF
Noise figure	NF	$V_{CE} = -6\text{V}, I_C = -0.3\text{mA}, R_g = 10\text{k}\Omega, f = 100\text{Hz}$		6	20	dB
Transition frequency	f_T	$V_{CE} = -6\text{V}, I_C = -10\text{mA}$	50			MHz

Marking

Marking	CS